

Discrete POWER & Signal **Technologies**

PN3638 PN3638A



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA. Sourced from Process 63. See PN2907A for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	25	V
V _{CBO}	Collector-Base Voltage	25	V
V _{EBO}	Emitter-Base Voltage	4.9	V
lc	Collector Current - Continuous	800	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		PN3638/A	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

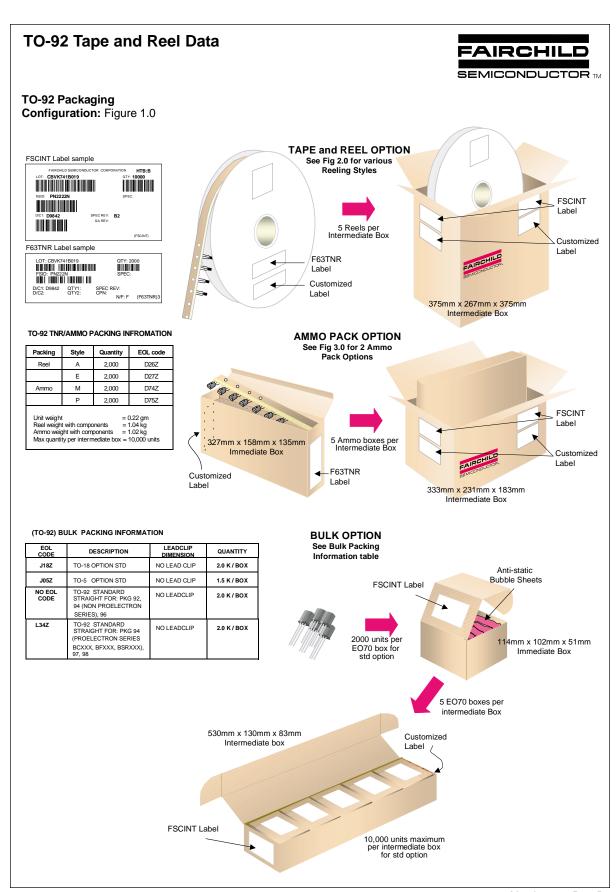
NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
- ,					
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	25		V
V _(BR) CES	Collector-Emitter Breakdown Voltage*	$I_C = 100 \mu\text{A}, I_B = 0$	25		V
V _(BR) CBO	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	25		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	4.0		V
Ices	Collector-Cutoff Current	V _{CE} = 15 V, I _E = 0 V _{CE} = 15 V, I _E = 0, T _A = 65°C		35 2.0	nA μA
ON CHAE	RACTERISTICS*				
h _{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 50 \text{ mA}$			
.4.5		PN3638	30		
		PN3638A	100		
		$V_{CE} = 2.0 \text{ V}, I_{C} = 300 \text{ mA}$ PN3638	30		
		PN3638A	20		
		$V_{CE} = 10 \text{ V}, I_{C} = 100 \text{ mA}$	00		
		PN3638 PN3638A	20 80		
		V _{CE} = 10 V, I _C = 1.0 mA	00		
		PN3638A	100		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 2.5 \text{ mA}$		0.25	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 2.5 \text{ mA}$		1.0	V
VBE(Sat)	Base Emiliar Salaration Vollage	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$	8.0	2.0	V
SMALL S	IGNAL CHARACTERISTICS				
Cob	Output Capacitance	V _{CB} = 10 V, f = 1.0 MHz		I	
		PN3638		20	pF
	Innut Conscitones	PN3638A		20 10	pF pF
Cib	Input Capacitance	PN3638A V _{BE} = 0.5 V, f = 1.0 MHz		10	pF
Cib	Input Capacitance	PN3638A			
	Input Capacitance Small-Signal Current Gain	PN3638A V _{BE} = 0.5 V, f = 1.0 MHz PN3638 PN3638A Ic = 50 mA, V _{CE} = 3.0 V,		10 65	pF pF
		PN3638A VBE = 0.5 V, f = 1.0 MHz PN3638 PN3638A Ic = 50 mA, VcE = 3.0 V, f = 100 MHz PN3638	1.0	10 65	pF pF
		PN3638A V _{BE} = 0.5 V, f = 1.0 MHz PN3638 PN3638A Ic = 50 mA, V _{CE} = 3.0 V,	1.0 1.5	10 65	pF pF
		PN3638A V _{BE} = 0.5 V, f = 1.0 MHz PN3638 PN3638A Ic = 50 mA, V _{CE} = 3.0 V, f = 100 MHz PN3638 PN3638A I _C = 10 mA, V _{CE} = 10 V, f = 1.0 kHz PN3638	1.5 25	10 65	pF pF
h _{fe}	Small-Signal Current Gain	PN3638A V _{BE} = 0.5 V, f = 1.0 MHz PN3638 PN3638A Ic = 50 mA, V _{CE} = 3.0 V, f = 100 MHz PN3638 PN3638A I _C = 10 mA, V _{CE} = 10 V, f = 1.0 kHz PN3638 PN3638A	1.5	65 25	pF pF pF
h _{fe}	Small-Signal Current Gain Input Impedance	$\begin{array}{c} \textbf{PN3638A} \\ \textbf{V}_{BE} = 0.5 \text{ V, f} = 1.0 \text{ MHz} \\ \textbf{PN3638} \\ \textbf{PN3638A} \\ \textbf{Ic} = 50 \text{ mA, V}_{CE} = 3.0 \text{ V, f} \\ \textbf{f} = 100 \text{ MHz} \\ \textbf{PN3638A} \\ \textbf{I}_{C} = 10 \text{ mA, V}_{CE} = 10 \text{ V, f} \\ \textbf{f} = 1.0 \text{ kHz} \\ \textbf{PN3638A} \\ \textbf{I}_{C} = 10 \text{ mA, V}_{CE} = 10 \text{ V, f} \\ \textbf{f} = 1.0 \text{ kHz} \\ \textbf{PN3638A} \\ \textbf{I}_{C} = 10 \text{ mA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text$	1.5 25	10 65 25 2.0	pF pF pF pF
h _{fe}	Small-Signal Current Gain Input Impedance Output Admittance	PN3638A VBE = 0.5 V, f = 1.0 MHz PN3638 PN3638A IC = 50 mA, VCE = 3.0 V, f = 100 MHz PN3638 PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638 PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638A	1.5 25	10 65 25 2.0 1.2	pF pF pF pF
Cib hfe hie hoe hre	Small-Signal Current Gain Input Impedance	$\begin{array}{c} \textbf{PN3638A} \\ \textbf{V}_{BE} = 0.5 \text{ V, f} = 1.0 \text{ MHz} \\ \textbf{PN3638} \\ \textbf{PN3638A} \\ \textbf{Ic} = 50 \text{ mA, V}_{CE} = 3.0 \text{ V, f} \\ \textbf{f} = 100 \text{ MHz} \\ \textbf{PN3638A} \\ \textbf{I}_{C} = 10 \text{ mA, V}_{CE} = 10 \text{ V, f} \\ \textbf{f} = 1.0 \text{ kHz} \\ \textbf{PN3638A} \\ \textbf{I}_{C} = 10 \text{ mA, V}_{CE} = 10 \text{ V, f} \\ \textbf{f} = 1.0 \text{ kHz} \\ \textbf{PN3638A} \\ \textbf{I}_{C} = 10 \text{ mA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text{ MA, V}_{CE} = 10 \text{ V, f} \\ \textbf{I}_{C} = 10 \text$	1.5 25	10 65 25 2.0	pF pF pF
h _{fe} h _{ie} h _{oe} h _{re}	Small-Signal Current Gain Input Impedance Output Admittance	PN3638A VBE = 0.5 V, f = 1.0 MHz PN3638 PN3638A IC = 50 mA, VCE = 3.0 V, f = 100 MHz PN3638 PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638 IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638A	1.5 25	2.0 1.2 26	pF pF pF pF
h _{fe} h _{ie} h _{oe} h _{re}	Small-Signal Current Gain Input Impedance Output Admittance Voltage Feedback Ratio	PN3638A VBE = 0.5 V, f = 1.0 MHz PN3638 PN3638A IC = 50 mA, VCE = 3.0 V, f = 100 MHz PN3638 PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638 IC = 10 mA, VCE = 10 V, F = 1.0 kHz PN3638A IC = 10 mA, VCE = 10 V, F = 1.0 kHz PN3638A	1.5 25	2.0 1.2 26	pF pF pF pF
h _{ie} h _{oe} h _{re} SWITCHI	Small-Signal Current Gain Input Impedance Output Admittance Voltage Feedback Ratio NG CHARACTERISTICS Turn-on Time	PN3638A VBE = 0.5 V, f = 1.0 MHz PN3638 PN3638A IC = 50 mA, VCE = 3.0 V, f = 100 MHz PN3638 PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638 PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638 PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638 PN3638A VCC = 10 V, IC = 300 mA,	1.5 25 100	2.0 1.2 26	pF pF pF pF kΩ μmhos x10 ⁻⁴ x10 ⁻⁴
h _{ie} h _{oe} hre SWITCHI ton	Small-Signal Current Gain Input Impedance Output Admittance Voltage Feedback Ratio NG CHARACTERISTICS Turn-on Time Delay Time	PN3638A VBE = 0.5 V, f = 1.0 MHz PN3638 PN3638A IC = 50 mA, VCE = 3.0 V, f = 100 MHz PN3638 PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638 IC = 10 mA, VCE = 10 V, F = 1.0 kHz PN3638A IC = 10 mA, VCE = 10 V, F = 1.0 kHz PN3638A	75 20	2.0 1.2 26	pF pF pF pF kΩ μmhos x10 ⁻⁴ x10 ⁻⁴
h _{fe} h _{ie} h _{oe} h _{re} SWITCHI ton td	Small-Signal Current Gain Input Impedance Output Admittance Voltage Feedback Ratio NG CHARACTERISTICS Turn-on Time Delay Time Rise Time	PN3638A VBE = 0.5 V, f = 1.0 MHz PN3638 PN3638A IC = 50 mA, VCE = 3.0 V, f = 100 MHz PN3638 IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638A VCC = 10 V, IC = 300 mA, IB1 = 30 mA	75 20 70	2.0 1.2 26	pF pF pF pF kΩ μmhos x10 ⁻⁴ x10 ⁻⁴
h _{ie} h _{oe} hre SWITCHI ton td tr	Small-Signal Current Gain Input Impedance Output Admittance Voltage Feedback Ratio NG CHARACTERISTICS Turn-on Time Delay Time Rise Time Turn-off Time	PN3638A VBE = 0.5 V, f = 1.0 MHz PN3638 PN3638A IC = 50 mA, VCE = 3.0 V, f = 100 MHz PN3638 PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638 PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638 PN3638A IC = 10 W, IC = 300 mA, IB1 = 30 mA VCC = 10 V, IC = 300 mA	75 20 70	2.0 1.2 26	pF pF pF pF kΩ μmhos x10 ⁻⁴ x10 ⁻⁴
h _{fe} h _{ie} h _{oe} h _{re}	Small-Signal Current Gain Input Impedance Output Admittance Voltage Feedback Ratio NG CHARACTERISTICS Turn-on Time Delay Time Rise Time	PN3638A VBE = 0.5 V, f = 1.0 MHz PN3638 PN3638A IC = 50 mA, VCE = 3.0 V, f = 100 MHz PN3638 IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638A IC = 10 mA, VCE = 10 V, f = 1.0 kHz PN3638A VCC = 10 V, IC = 300 mA, IB1 = 30 mA	75 20 70	2.0 1.2 26	pF pF pF pF kΩ μmhos x10 ⁻⁴ x10 ⁻⁴

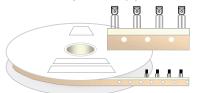


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TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



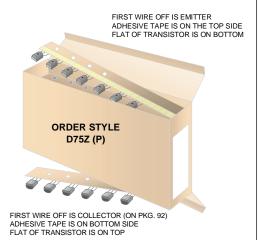
Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

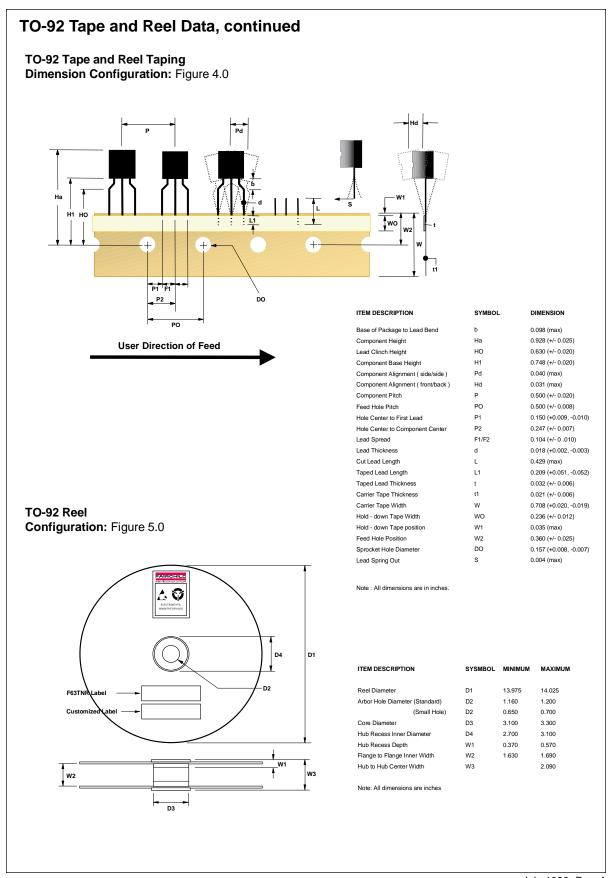
Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





September 1999, Rev. B



TO-92 Package Dimensions FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 B F В В В D D 2 В S С G Ε Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

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0.095 0.084 2.13

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Rev. G